### ISC4356AS1

FOR HIGH CURRENT DRIVE APPLICATION SILICON NPN EPITAXIAL TYPE

### **DESCRIPTION**

ISC4356AS1 is a silicon NPN epitaxial type transistor designed relay drive application.

### **FEATURE**

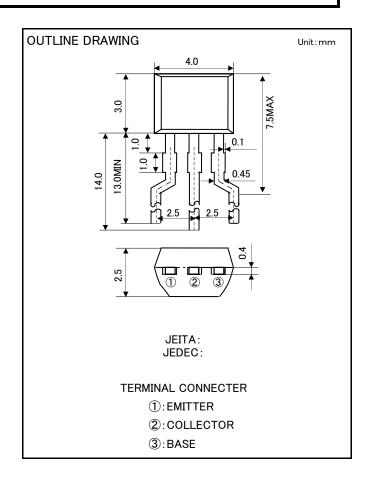
- High voltage. V<sub>CEo</sub>=60V
- ullet High collector current.  $I_c$ =2A
- $\bullet \text{Low V}_{\text{CE}}(\text{sat}) \quad \text{V}_{\text{CE}}(\text{sat}) = 0.5 \text{V max } (@I_{\text{C}} = 1 \text{A, } I_{\text{B}} = 50 \text{mA})$
- High collector dissipation. P<sub>c</sub>=600mW

### **APPLICATION**

Audio machine, VCR, relay drive.

### MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit	
Vcво	Collector to Base voltage	60	V	
VEBO	Emitter to Base voltage	6	٧	
VCEO	Collector to Emitter voltage	60	<b>V</b>	
$I_{\rm C}$	Collector current	2	Α	
I <sub>CM</sub>	Peak collector current	3	Α	
P <sub>c</sub>	Collector dissipation	600	mW	
$T_{j}$	Junction temperature	+150	ပ္	
$T_{stg}$	Storage temperature	−55 <b>~</b> +150	°C	



### ELECTRICAL CHARACTERISTICS (Ta=25°C)

Damanatan	Parameter	T		Limits		11.5
Parameter		Test conditions	Min	Тур	Max	Unit
V(BR)cBo	C to B break down voltage	$I_{C}$ = 10 $\mu$ A , $I_{E}$ =0mA	60	-	-	٧
V(BR)EBO	E to B break down voltage	$I_{\rm E}$ = 10 $\mu$ A , $I_{\rm C}$ =0mA	6	-	-	٧
V(BR)ceo	C to E break down voltage	I <sub>C</sub> = 2mA , RBE= ∞	60	-	-	٧
ICBO	Collector cut off current	V <sub>CB</sub> = 50V , I <sub>E</sub> = 0mA	-	-	0.2	μΑ
IEBO	Emitter cut off current	$V_{EB} = 4V$ , $I_{C} = 0mA$	-	-	0.2	μΑ
hFE※	DC forward current gain	$V_{CE} = 4V$ , $I_{C} = 100$ mA	55	-	300	-
VCE(sat)	C to E Saturation Voltage	I <sub>C</sub> =1A , I <sub>B</sub> = 50mA	_	0.2	0.5	٧
fT	Gain band width product	V <sub>CE</sub> = 10V , I <sub>E</sub> = -10mA	-	80	-	MHz
Cob	Collector output capacitance	V <sub>CB</sub> = 10V , I <sub>E</sub> = 0mA,f=1MHz	-	18	-	pF

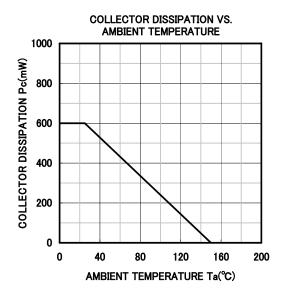
※) It shows hFE classification in right table.

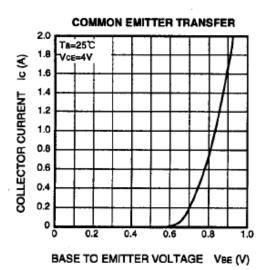
Item	С	D	Е	
hFE item	55~110	90~180	150~300	

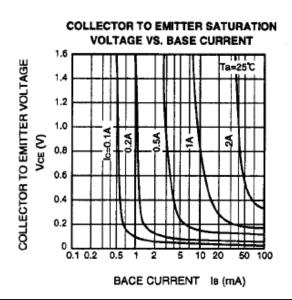
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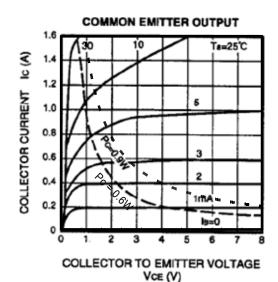
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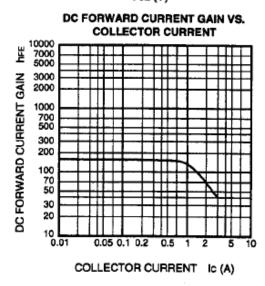
#### TYPICAL CHARACTERISTICS

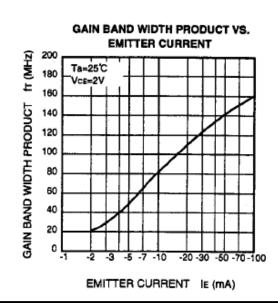








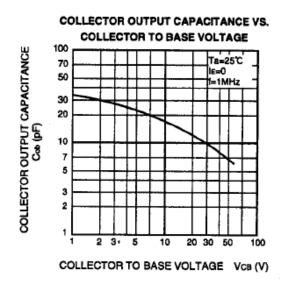




⟨SMALL-SIGNAL TRANSISTOR⟩

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FOR HIGH CURRENT DRIVE APPLICATION SILICON NPN EPITAXIAL TYPE





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